



ALTERNATIVE TO PTO/SB/08a/b (06-03)

Substitute for form 1449/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Application Number	10/681,108-Conf. #8110
				Filing Date	October 9, 2003
				First Named Inventor	Chandra Mouli
				Art Unit	2811 2829 2891
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	M4065.0762/P762

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶

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NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ²
LT	AA	P. BOULON et al., "Anomalous Short Channel Effects in Indium Implanted nMOSFETS," 1997 IEEE.			
LT	AB	Y. LEE et al., "Indium Doped nMOSFETs and Buried Channel pMOSFETs with n+ Polysilicon Gate," Jpn. J. Appl. Phys. Vol. 36 (1997), pp. 1341-1345.			
LT	AC	I. C. KIZILYALLI et al., "n+ Polysilicon Gate PMOSFET's with Indium Doped Buried-Channels," IEEE Electron Device Letters, Vol. 17 (1996), pp. 46-49.			
LT	AD	G. G. SHAHIDI, "Indium Channel Implants for Improved MOSFET Behavior at the 100-nm Channel Length Regime," IEEE Transactions on Electronic Devices, Vol. 36 (1989) p. 2605.			
LT	AE	H. TIAN et al., "A Comparative Study of Indium and Boron Implanted Silicon Bipolar Transistors," IEEE Transactions on Electron Devices, Vol. 48 (2001), pp.2520-2524			

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Luan Thai

3/14/05